

Features:

- 650V Schottky Diode •
- Zero Reverse Recovery Current .
- High Frequency Operation •
- Positive Temperature Coefficient ٠
- Temperature independent • Switching

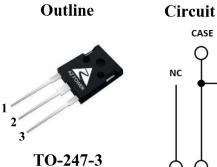
Applications:

- Switch Mode Power Supply •
- Booster diodes in PFC, DC/DC •
- AC/DC converters

B	en	efi	ts:

- Unipolar Rectifier •
- Minimal switching loss .
- Higher Efficiency •
- Low cooling requirement •

Symbol	Value	Unit		
V _{RRM}	650	V		
$I_F \ (T_c = 156^{\circ}C)$	15	А		
Qc	34	nC		



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Symbol	Parameter	Value	Unit	Test Conditions
VR	DC Peak Reverse Voltage	650	V	$T_J = 25^{\circ}C$
V _{RRM}	Repetitive Peak Reverse	650	V	$T_J = 25^{\circ}C$
V _{RSM}	Surge Peak Reverse Voltage	650	V	$T_J = 25^{\circ}C$
IF	Continuous Forward Current	53 25 15	А	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 135^{\circ}{\rm C}$ $T_{\rm C} = 156^{\circ}{\rm C}$
I _{FRM}	Repetitive Peak Forward Surge Current	91 81	А	$T_{\rm C} = 25^{\circ}$ C, $T_{\rm P} = 10$ ms, Half Sine Wave Tc = 110°C, $T_{\rm P} = 10$ ms, Half Sine Wave
I _{FSM}	Non-Repetitive Peak Forward Surge Current	120 109	A	$T_{\rm C} = 25^{\circ}$ C, $T_{\rm P} = 10$ ms, Half Sine Wave Tc = 110°C, $T_{\rm P} = 10$ ms, Half Sine Wave
PD	Power Dissipation	227 98	W	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 110^{\circ}{\rm C}$
T _{J,max}	Operating Junction Temperature	175	°C	
T _{stg}	Storage Temperature Range	-55 to 175	°C	

Maximum Ratings

S4D065V015S, Rev. 1.0



Thermal characteristics

Symbol	Parameter	Min.	Тур.	Max.	Unit
RthJC	Thermal resistance		0.66		°C/W

Electrical Characteristics

Symbol	Parameter	Value		T ⊺ : 4		
		Min.	Тур.	Max.	Unit	Test Conditions
VDC	DC Blocking Voltage	650			V	$I_R = 100 \mu A, T_J = 25^{\circ}C$
V _F	Forward Voltage		1.45	1.7	V	$I_F = 15A, T_J = 25^{\circ}C$
▼ F			1.8	2.1		$I_F = 15A, T_J = 175^{\circ}C$
I _R	Reverse Current		5	100	μΑ	$V_{R} = 650V, T_{J} = 25^{\circ}C$
			10	200		$V_R = 650V, T_J = 175^{\circ}C$
Qc	Total Capacitive Charge		34]		$I_{\rm F} = 15$ A, dI/dt = 350A/µs
					nC	$T_J = 25^{\circ}C, V_R = 400V$
С	Total Capacitance		644		pF	$V_{R} = 1V, T_{J} = 25^{\circ}C, f = 1 \text{ MHz}$
			88			V_R =200V, T_J =25°C, f=1 MHz
			85			V_R =400V, T_J =25°C, f=1 MHz

Typical Performance

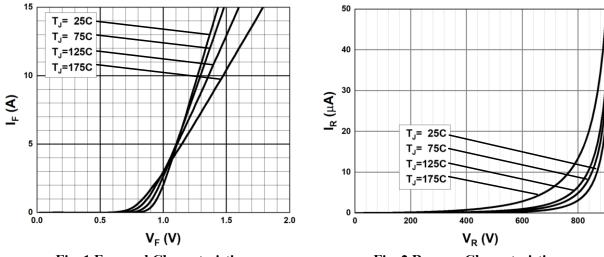
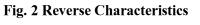


Fig. 1 Forward Characteristics



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Typical Performance

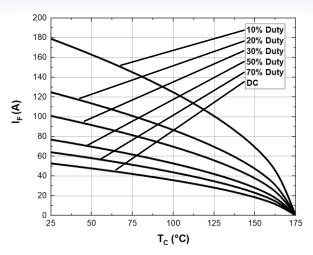
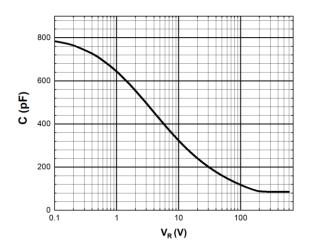
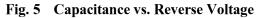


Fig. 3 Current Derating





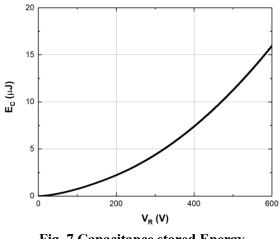
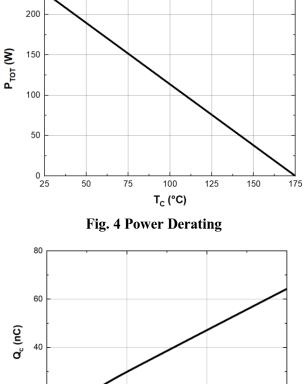


Fig. 7 Capacitance stored Energy



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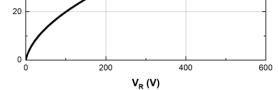


Fig. 6 Recovery Charge vs. Reverse Voltage

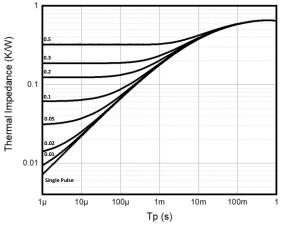
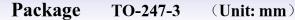
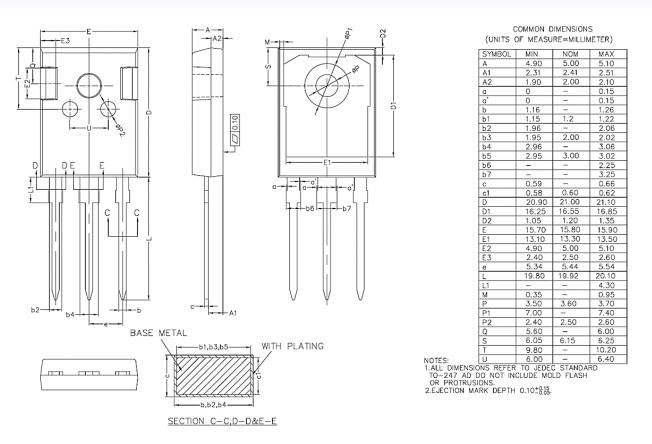


Fig. 8 Thermal Impendance







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